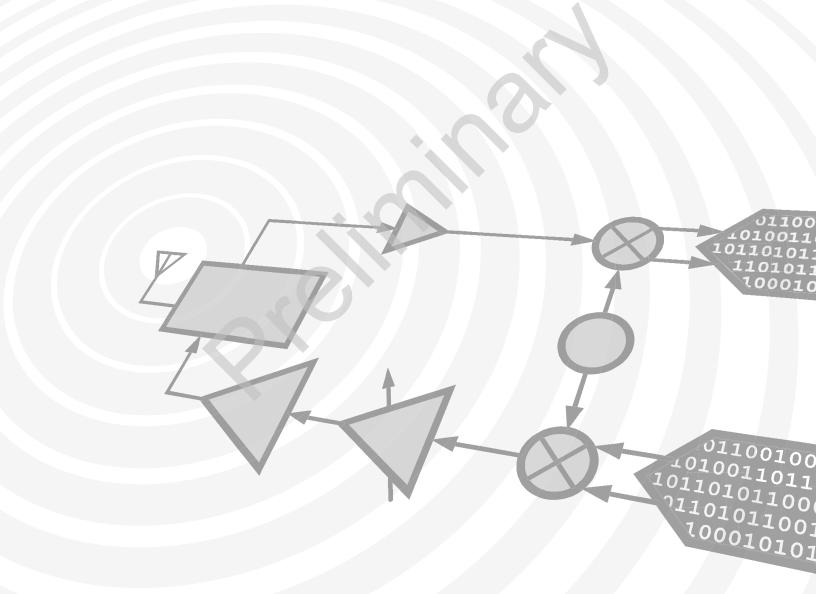




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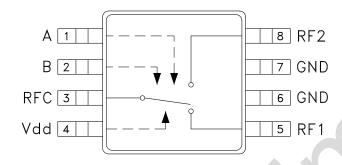
# GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

# Typical Applications

The HMC574AMS8 / HMC574AMS8E is ideal for:

- Cellular/3G Infrastructure
- Private Mobile Radio Handsets
- WLAN, WiMAX & WiBro
- Automotive Telematics
- Test Equipment

# **Functional Diagram**



### **Features**

Low Insertion Loss: 0.3 dB

High Third Order Intercept: +65 dBm

Isolation: 30 dB

Single Positive Supply: +3 to +8V

SMT Package: MSOP8

Included in the HMC-DK005 Designer's Kit

# **General Description**

The HMC574AMS8 & HMC574AMS8E are low-cost SPDT switches in 8-lead MSOP packages for use in transmit/receive applications which require very low distortion at high incident power levels. The device can control signals from DC to 3 GHz and is especially suited for Cellular/3G infrastructure, WiMAX and WiBro applications with only 0.3 dB typical insertion loss. The design provides 5 watt power handling performance and +65 dBm third order intercept at +8 Volt bias. RF1 and RF2 are reflective shorts when "Off".

# Electrical Specifications,

 $T_A = +25^{\circ}$  C, VctI = 0/+5 Vdc, Vdd = +5 Vdc (Unless Otherwise Stated), 50 Ohm System

Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		0.25 0.3 0.4 0.5	0.5 0.6 0.7 0.8	dB dB dB dB
Isolation		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz	26 24 21 16	30 28 25 20		dB dB dB dB
Return Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		35 25 18 16		dB dB dB dB
Input Power for 1dB Compression	VctI = 0/+3V VctI = 0/+5V VctI = 0/+8V	0.5 - 3.0 GHz	33 35 37	36 38 39		dBm dBm dBm
Input Third Order Intercept (Two-tone Input Power = +27 dBm Each Tone)	VctI = 0/+3V VctI = 0/+5V VctI = 0/+8V	0.5 - 3.0 GHz		55 63 65		dBm dBm dBm
	SE, tFALL (10/90% RF) 0% CTL to 10/90% RF)	DC - 3.0 GHz		80 120		ns ns

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# GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

## **Absolute Maximum Ratings**

Max. Input Power $V_{dd} = 0/+8V$	0.5 - 2.5 GHz	39 dBm	
Bias Voltage Range (Vdd)		-0.2 to +10 Vdc	
Control Voltage Range (A & B)		-0.2 to +Vdd Vdc	
Hot Switching Power Level V <sub>dd</sub> = +8V		39 dBm	
Channel Temperature		150 °C	
Continuous Pdiss ( T= + 85 °C) (derate 10 mW/°C above 85 °C)		0.65W	
Thermal Resistance		100 °C/W	
Storage Temperature		-65 to +150 °C	
Operating Temperature		-40 to +85 °C	
ESD Sensitivity (H	BM)	Class 1A	

DC Blocks are required at ports RFC, RF1 and RF2



### Bias Voltage & Current

Vdd (Vdc)	Typical Idd (μA)	
+3	2	
+5	10	
+8	40	

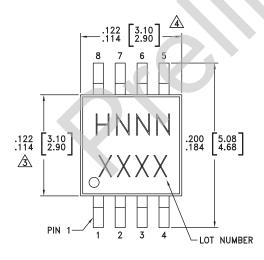
## **Control Voltages**

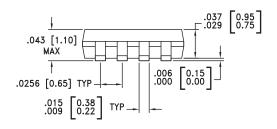
	State	Bias Condition	
	Low	0 to +0.2 Vdc @ 10 μA Typical	
High		Vdd ± 0.2 Vdc @ 10 μA Typical	

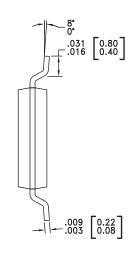
# **Truth Table**

Control Input (Vctl)		Signal Path State		
А	В	RFC to RF1	RFC to RF2	
High	Low	Off	On	
Low	High	On	Off	

# **Outline Drawing**







### NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 5. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.